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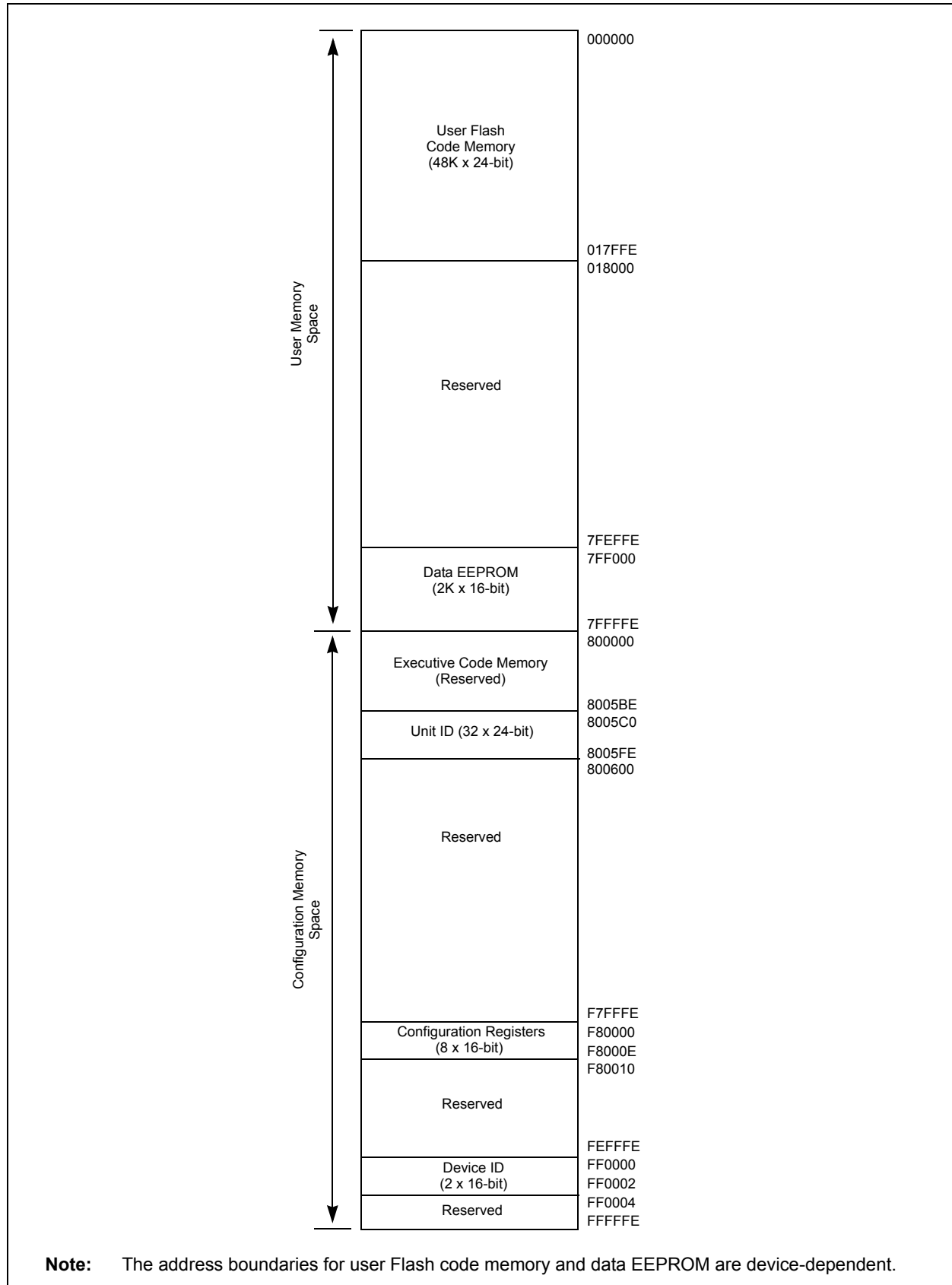
Applications of "[Embedded - Microcontrollers](#)"

Details

| | |
|----------------------------|---|
| Product Status | Obsolete |
| Core Processor | dsPIC |
| Core Size | 16-Bit |
| Speed | 20 MIPS |
| Connectivity | CANbus, I ² C, SPI, UART/USART |
| Peripherals | Brown-out Detect/Reset, LVD, Motor Control PWM, QEI, POR, PWM, WDT |
| Number of I/O | 68 |
| Program Memory Size | 144KB (48K x 24) |
| Program Memory Type | FLASH |
| EEPROM Size | 4K x 8 |
| RAM Size | 8K x 8 |
| Voltage - Supply (Vcc/Vdd) | 2.5V ~ 5.5V |
| Data Converters | A/D 16x10b |
| Oscillator Type | Internal |
| Operating Temperature | -40°C ~ 85°C (TA) |
| Mounting Type | Surface Mount |
| Package / Case | 80-TQFP |
| Supplier Device Package | 80-TQFP (14x14) |
| Purchase URL | https://www.e-xfl.com/product-detail/microchip-technology/dspic30f6010t-20i-pf |

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FIGURE 2-2: PROGRAM MEMORY MAP



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5.5.3 PROGRAMMING VERIFICATION

Once code memory is programmed, the contents of memory can be verified to ensure that programming was successful. Verification requires code memory to be read back and compared against the copy held in the programmer's buffer.

The `READP` command can be used to read back all the programmed code memory.

Alternatively, you can have the programmer perform the verification once the entire device is programmed using a checksum computation, as described in [Section 6.8 "Checksum Computation"](#).

5.6 Data EEPROM Programming

5.6.1 OVERVIEW

The panel architecture for the data EEPROM memory array consists of 128 rows of sixteen 16-bit data words. Each panel stores 2K words. All devices have either one or no memory panels. Devices with data EEPROM provide either 512 words, 1024 words or 2048 words of memory on the one panel (see [Table 5-3](#)).

TABLE 5-3: DATA EEPROM SIZE

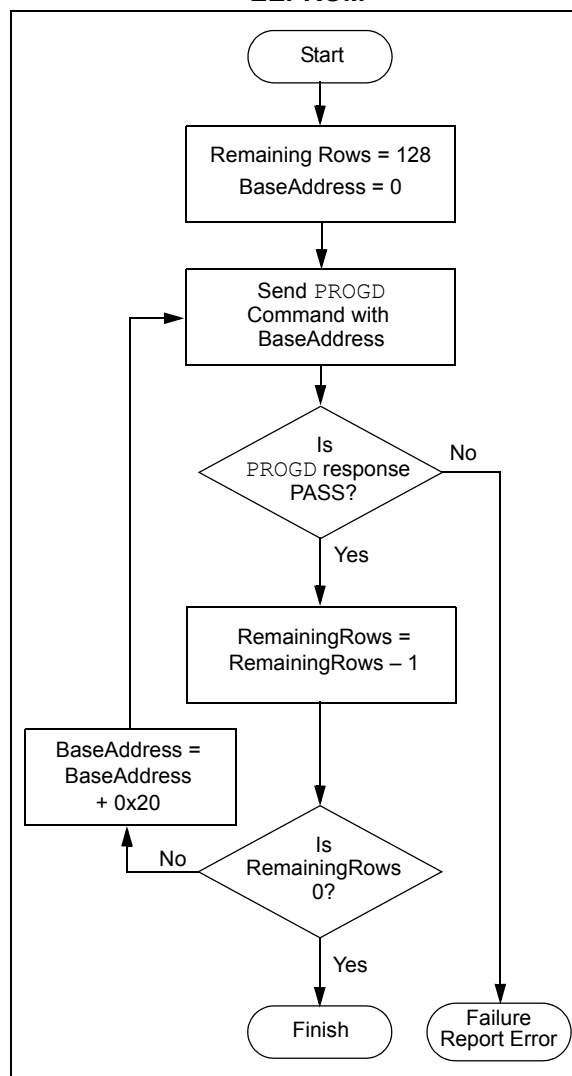
| Device | Data EEPROM Size (Words) | Number of Rows |
|---------------|--------------------------|----------------|
| dsPIC30F2010 | 512 | 32 |
| dsPIC30F2011 | 0 | 0 |
| dsPIC30F2012 | 0 | 0 |
| dsPIC30F3010 | 512 | 32 |
| dsPIC30F3011 | 512 | 32 |
| dsPIC30F3012 | 512 | 32 |
| dsPIC30F3013 | 512 | 32 |
| dsPIC30F3014 | 512 | 32 |
| dsPIC30F4011 | 512 | 32 |
| dsPIC30F4012 | 512 | 32 |
| dsPIC30F4013 | 512 | 32 |
| dsPIC30F5011 | 512 | 32 |
| dsPIC30F5013 | 512 | 32 |
| dsPIC30F5015 | 512 | 32 |
| dsPIC30F5016 | 512 | 32 |
| dsPIC30F6010 | 2048 | 128 |
| dsPIC30F6010A | 2048 | 128 |
| dsPIC30F6011 | 1024 | 64 |
| dsPIC30F6011A | 1024 | 64 |
| dsPIC30F6012 | 2048 | 128 |
| dsPIC30F6012A | 2048 | 128 |
| dsPIC30F6013 | 1024 | 64 |
| dsPIC30F6013A | 1024 | 64 |
| dsPIC30F6014 | 2048 | 128 |
| dsPIC30F6014A | 2048 | 128 |
| dsPIC30F6015 | 2048 | 128 |

5.6.2 PROGRAMMING METHODOLOGY

The programming executive uses the `PROGD` command to program the data EEPROM. [Figure 5-4](#) illustrates the flowchart of the process. Firstly, the number of rows to program (RemainingRows) is based on the device size, and the destination address (BaseAddress) is set to '0'. In this example, 128 rows (2048 words) of data EEPROM will be programmed.

The first `PROGD` command programs the first row of data EEPROM. Once the command completes successfully, 'RemainingRows' is decremented by 1 and compared with 0. Since there are 127 more rows to program, 'BaseAddress' is incremented by 0x20 to point to the next row of data EEPROM. This process is then repeated until all 128 rows of data EEPROM are programmed.

FIGURE 5-4: FLOWCHART FOR PROGRAMMING dsPIC30F6014A DATA EEPROM



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TABLE 5-6: FOSC CONFIGURATION BITS DESCRIPTION FOR dsPIC30F2011/2012, dsPIC30F3010/3011/3012/3013/3014, dsPIC30F4013, dsPIC30F5015/5016, dsPIC30F6010A/6011A/6012A/6013A/6014A AND dsPIC30F6015

| Bit Field | Register | Description |
|------------|----------|---|
| FCKSM<1:0> | FOSC | Clock Switching Mode 1x = Clock switching is disabled, Fail-Safe Clock Monitor is disabled 01 = Clock switching is enabled, Fail-Safe Clock Monitor is disabled 00 = Clock switching is enabled, Fail-Safe Clock Monitor is enabled |
| FOS<2:0> | FOSC | Oscillator Source Selection on POR 111 = Primary Oscillator 110 = Reserved 101 = Reserved 100 = Reserved 011 = Reserved 010 = Internal Low-Power RC Oscillator 001 = Internal Fast RC Oscillator (no PLL) 000 = Low-Power 32 kHz Oscillator (Timer1 Oscillator) |
| FPR<4:0> | FOSC | Primary Oscillator Mode (when FOS<2:0> = 111b) 11xxx = Reserved (do not use) 10111 = HS/3 w/PLL 16X – HS/3 crystal oscillator with 16X PLL (10 MHz-25 MHz crystal) 10110 = HS/3 w/PLL 8X – HS/3 crystal oscillator with 8X PLL (10 MHz-25 MHz crystal) 10101 = HS/3 w/PLL 4X – HS/3 crystal oscillator with 4X PLL (10 MHz-25 MHz crystal) 10100 = Reserved (do not use) 10011 = HS/2 w/PLL 16X – HS/2 crystal oscillator with 16X PLL (10 MHz-25 MHz crystal) 10010 = HS/2 w/PLL 8X – HS/2 crystal oscillator with 8X PLL (10 MHz-25 MHz crystal) 10001 = HS/2 w/PLL 4X – HS/2 crystal oscillator with 4X PLL (10 MHz-25 MHz crystal) 10000 = Reserved (do not use) 01111 = ECIO w/PLL 16x – External clock with 16x PLL. OSC2 pin is I/O 01110 = ECIO w/PLL 8x – External clock with 8x PLL. OSC2 pin is I/O 01101 = ECIO w/PLL 4x – External clock with 4x PLL. OSC2 pin is I/O 01100 = Reserved (do not use) 01011 = Reserved (do not use) 01010 = FRC w/PLL 8x – Internal fast RC oscillator with 8x PLL. OSC2 pin is I/O 01001 = Reserved (do not use) 01000 = Reserved (do not use) 00111 = XT w/PLL 16X – XT crystal oscillator with 16X PLL 00110 = XT w/PLL 8X – XT crystal oscillator with 8X PLL 00101 = XT w/PLL 4X – XT crystal oscillator with 4X PLL 00100 = Reserved (do not use) 00011 = FRC w/PLL 16x – Internal fast RC oscillator with 8x PLL. OSC2 pin is I/O 00010 = Reserved (do not use) 00001 = FRC w/PLL 4x – Internal fast RC oscillator with 4x PLL. OSC2 pin is I/O 00000 = Reserved (do not use) |

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TABLE 5-6: FOSC CONFIGURATION BITS DESCRIPTION FOR dsPIC30F2011/2012, dsPIC30F3010/3011/3012/3013/3014, dsPIC30F4013, dsPIC30F5015/5016, dsPIC30F6010A/6011A/6012A/6013A/6014A AND dsPIC30F6015 (CONTINUED)

| Bit Field | Register | Description |
|-----------|----------|--|
| FPR<4:0> | FOSC | Alternate Oscillator Mode (when FOS<2:0> = 011b) 1xxxx = Reserved (do not use) 0111x = Reserved (do not use) 01101 = Reserved (do not use) 01100 = ECIO – External clock. OSC2 pin is I/O 01011 = EC – External clock. OSC2 pin is system clock output (Fosc/4) 01010 = Reserved (do not use) 01001 = ERC – External RC oscillator. OSC2 pin is system clock output (Fosc/4) 01000 = ERCIO – External RC oscillator. OSC2 pin is I/O 00111 = Reserved (do not use) 00110 = Reserved (do not use) 00101 = Reserved (do not use) 00100 = XT – XT crystal oscillator (4 MHz-10 MHz crystal) 00010 = HS – HS crystal oscillator (10 MHz-25 MHz crystal) 00001 = Reserved (do not use) 00000 = XTL – XTL crystal oscillator (200 kHz-4 MHz crystal) |

TABLE 5-8: dsPIC30F CONFIGURATION REGISTERS (FOR dsPIC30F2010, dsPIC30F4011/4012 AND dsPIC30F6010/ 6011/6012/6013/ 6014)

| Address | Name | Bit 15 | Bit 14 | Bit 13 | Bit 12 | Bit 11 | Bit 10 | Bit 9 | Bit 8 | Bit 7 | Bit 6 | Bit 5 | Bit 4 | Bit 3 | Bit 2 | Bit 1 | Bit 0 |
|----------|---------|------------|--------|-------------------------|--------|--------|-----------------------|-------------------------|-------------------------|-------|-------|------------|-------|-------------------------|-------------------------|------------|-------|
| 0xF80000 | FOSC | FCKSM<1:0> | | — | — | — | — | FOS<1:0> | | — | — | — | — | FPR<3:0> | | | |
| 0xF80002 | FWDT | FWDTEN | — | — | — | — | — | — | — | — | — | FWPSA<1:0> | | FWPSB<3:0> | | | |
| 0xF80004 | FBORPOR | MCLREN | — | — | — | — | PWMPIN ⁽¹⁾ | HPOL ⁽¹⁾ | LPOL ⁽¹⁾ | BOREN | — | BORV<1:0> | | — | — | FPWRT<1:0> | |
| 0xF80006 | FBS | — | — | Reserved ⁽²⁾ | | — | — | — | Reserved ⁽²⁾ | — | — | — | — | Reserved ⁽²⁾ | | | |
| 0xF80008 | FSS | — | — | Reserved ⁽²⁾ | | — | — | Reserved ⁽²⁾ | | — | — | — | — | Reserved ⁽²⁾ | | | |
| 0xF8000A | FGS | — | — | — | — | — | — | — | — | — | — | — | — | — | Reserved ⁽²⁾ | GCP | GWRP |
| 0xF8000C | FICD | BKBUG | COE | — | — | — | — | — | — | — | — | — | — | — | — | ICS<1:0> | |

Note 1: On the 6011, 6012, 6013 and 6014, these bits are reserved (read as '1' and must be programmed as '1').

Note 2: Reserved bits read as '1' and must be programmed as '1'.

TABLE 5-9: dsPIC30F CONFIGURATION REGISTERS (FOR dsPIC30F5011/5013)

| Address | Name | Bit 15 | Bit 14 | Bit 13 | Bit 12 | Bit 11 | Bit 10 | Bit 9 | Bit 8 | Bit 7 | Bit 6 | Bit 5 | Bit 4 | Bit 3 | Bit 2 | Bit 1 | Bit 0 |
|----------|---------|------------|--------|----------|--------|--------|-------------------------|----------|-------|-------|-------|------------|-------|------------|----------|------------|-------|
| 0xF80000 | FOSC | FCKSM<1:0> | | — | — | — | — | FOS<1:0> | | — | — | — | — | FPR<3:0> | | | |
| 0xF80002 | FWDT | FWDTEN | — | — | — | — | — | — | — | — | — | FWPSA<1:0> | | FWPSB<3:0> | | | |
| 0xF80004 | FBORPOR | MCLREN | — | — | — | — | Reserved ⁽¹⁾ | | | BOREN | — | BORV<1:0> | | — | — | FPWRT<1:0> | |
| 0xF80006 | FBS | — | — | RBS<1:0> | | — | — | — | EBS | — | — | — | — | BSS<2:0> | | | BWRP |
| 0xF80008 | FSS | — | — | RSS<1:0> | | — | — | ESS<1:0> | | — | — | — | — | SSS<2:0> | | | SWRP |
| 0xF8000A | FGS | — | — | — | — | — | — | — | — | — | — | — | — | — | GSS<1:0> | | GWRP |
| 0xF8000C | FICD | BKBUG | COE | — | — | — | — | — | — | — | — | — | — | — | — | ICS<1:0> | |

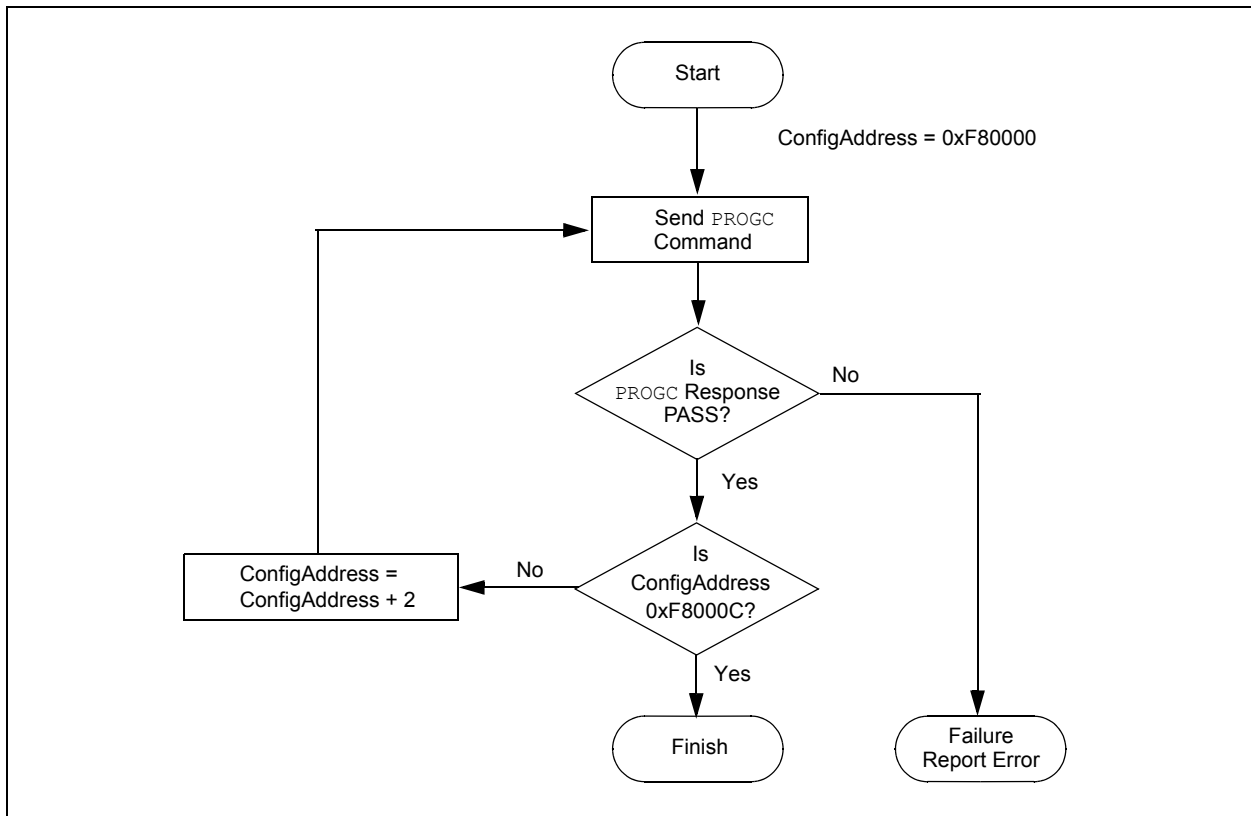
Note 1: Reserved bits read as '1' and must be programmed as '1'.

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5.8 Exiting Enhanced ICSP Mode

The Enhanced ICSP mode is exited by removing power from the device or bringing MCLR to VIL. When normal user mode is next entered, the program that was stored using Enhanced ICSP will execute.

FIGURE 5-5: CONFIGURATION BIT PROGRAMMING FLOW



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6.0 OTHER PROGRAMMING FEATURES

6.1 Erasing Memory

Memory is erased by using an `ERASEB`, `ERASED` or `ERASEP` command, as detailed in [Section 8.5 “Command Descriptions”](#). Code memory can be erased by row using `ERASEP`. Data EEPROM can be erased by row using `ERASED`. When memory is erased, the affected memory locations are set to ‘1’s.

`ERASEB` provides several Bulk Erase options. Performing a Chip Erase with the `ERASEB` command clears all code memory, data EEPROM and code protection registers. Alternatively, `ERASEB` can be used to selectively erase either all code memory or data EEPROM. Erase options are summarized in [Table 6-1](#).

TABLE 6-1: ERASE OPTIONS

| Command | Affected Region |
|------------------------------------|---|
| <code>ERASEB</code> | Entire chip ⁽¹⁾ or all code memory or all data EEPROM, or erase by segment |
| <code>ERASED</code> | Specified rows of data EEPROM |
| <code>ERASEP</code> ⁽²⁾ | Specified rows of code memory |

- Note 1:** The system operation Configuration registers and device ID registers are not erasable.
- 2:** `ERASEP` cannot be used to erase code-protect Configuration bits. These bits must be erased using `ERASEB`.

6.2 Modifying Memory

Instead of bulk-erasing the device before programming, it is possible that you may want to modify only a section of an already programmed device. In this situation, Chip Erase is not a realistic option.

Instead, you can erase selective rows of code memory and data EEPROM using `ERASEP` and `ERASED`, respectively. You can then reprogram the modified rows with the `PROGP` and `PROGD` command pairs. In these cases, when code memory is programmed, single-panel programming must be specified in the `PROGP` command.

For modification of Advanced Code Protection bits for a particular segment, the entire chip must first be erased with the `ERASEB` command. Alternatively, on devices that support Advanced Security, individual segments (code and/or data EEPROM) may be erased, by suitably changing the MS (Memory Select)

field in the `ERASEB` command. The code-protect Configuration bits can then be reprogrammed using the `PROGC` command.

Note: If read or write code protection is enabled for a segment, no modifications can be made to that segment until code protection is disabled. Code protection can only be disabled by performing a Chip Erase or by performing a Segment Erase operation for the required segment.

6.3 Reading Memory

The `READD` command reads the data EEPROM, Configuration bits and device ID of the device. This command only returns 16-bit data and operates on 16-bit registers. `READD` can be used to return the entire contents of data EEPROM.

The `READP` command reads the code memory of the device. This command only returns 24-bit data packed as described in [Section 8.3 “Packed Data Format”](#). `READP` can be used to read up to 32K instruction words of code memory.

Note: Reading an unimplemented memory location causes the programming executive to reset. All `READD` and `READP` commands **must** specify only valid memory locations.

6.4 Programming Executive Software Version

At times, it may be necessary to determine the version of programming executive stored in executive memory. The `QVER` command performs this function. See [Section 8.5.11 “QVER Command”](#) for more details about this command.

6.5 Data EEPROM Information in the Hexadecimal File

To allow portability of code, the programmer must read the data EEPROM information from the hexadecimal file. If data EEPROM information is not present, a simple warning message should be issued by the programmer. Similarly, when saving a hexadecimal file, all data EEPROM information must be included. An option to not include the data EEPROM information can be provided.

Microchip Technology Inc. believes that this feature is important for the benefit of the end customer.

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TABLE 8-1: PROGRAMMING EXECUTIVE COMMAND SET

| Opcode | Mnemonic | Length (16-bit words) | Time Out | Description |
|--------|-----------------------|-----------------------------|----------|---|
| 0x0 | SCHECK | 1 | 1 ms | Sanity check. |
| 0x1 | READD | 4 | 1 ms/row | Read N 16-bit words of data EEPROM, Configuration registers or device ID starting from specified address. |
| 0x2 | READP | 4 | 1 ms/row | Read N 24-bit instruction words of code memory starting from specified address. |
| 0x3 | Reserved | N/A | N/A | This command is reserved. It will return a NACK. |
| 0x4 | PROGD ⁽²⁾ | 19 | 5 ms | Program one row of data EEPROM at the specified address, then verify. |
| 0x5 | PROGP ⁽¹⁾ | 51 | 5 ms | Program one row of code memory at the specified address, then verify. |
| 0x6 | PROGC | 4 | 5 ms | Write byte or 16-bit word to specified Configuration register. |
| 0x7 | ERASEB | 2 | 5 ms | Bulk Erase (entire code memory or data EEPROM), or erase by segment. |
| 0x8 | ERASED ⁽²⁾ | 3 | 5 ms/row | Erase rows of data EEPROM from specified address. |
| 0x9 | ERASEP ⁽¹⁾ | 3 | 5 ms/row | Erase rows of code memory from specified address. |
| 0xA | QBLANK | 3 | 300 ms | Query if the code memory and data EEPROM are blank. |
| 0xB | QVER | 1 | 1 ms | Query the programming executive software version. |

- Note 1:** One row of code memory consists of (32) 24-bit words. Refer to [Table 5-2](#) for device-specific information.
Note 2: One row of data EEPROM consists of (16) 16-bit words. Refer to [Table 5-3](#) for device-specific information.

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8.5 Command Descriptions

All commands that are supported by the programming executive are described in [Section 8.5.1 “SCHECK Command”](#) through [Section 8.5.11 “QVER Command”](#).

8.5.1 SCHECK COMMAND

| | | | |
|--------|--------|----|---|
| 15 | 12 | 11 | 0 |
| Opcode | Length | | |

| Field | Description |
|--------|-------------|
| Opcode | 0x0 |
| Length | 0x1 |

The `SCHECK` command instructs the programming executive to do nothing, but generate a response. This command is used as a “sanity check” to verify that the programming executive is operational.

Expected Response (2 words):

0x1000
0x0002

Note: This instruction is not required for programming, but is provided for development purposes only.

8.5.2 READD COMMAND

| | | | | | |
|-----------|----|--------|----------|---|---|
| 15 | 12 | 11 | 8 | 7 | 0 |
| Opcode | | Length | | | |
| Reserved0 | | N | | | |
| Reserved1 | | | Addr_MSB | | |
| Addr_LS | | | | | |

| Field | Description |
|-----------|--|
| Opcode | 0x1 |
| Length | 0x4 |
| Reserved0 | 0x0 |
| N | Number of 16-bit words to read (max of 2048) |
| Reserved1 | 0x0 |
| Addr_MSB | MSB of 24-bit source address |
| Addr_LS | LS 16 bits of 24-bit source address |

The `READD` command instructs the programming executive to read N 16-bit words of memory starting from the 24-bit address specified by `Addr_MSB` and `Addr_LS`. This command can only be used to read 16-bit data. It can be used to read data EEPROM, Configuration registers and the device ID.

Expected Response (2+N words):

0x1100
N + 2
Data word 1
...
Data word N

Note: Reading unimplemented memory will cause the programming executive to reset.

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9.2.3 QE_Code FIELD

The QE_Code is a byte in the first word of the response. This byte is used to return data for query commands, and error codes for all other commands.

When the programming executive processes one of the two query commands (`QBLANK` or `QVER`), the returned opcode is always PASS and the QE_Code holds the query response data. The format of the QE_Code for both queries is shown in [Table 9-3](#).

TABLE 9-3: QE_Code FOR QUERIES

| Query | QE_Code |
|--------|---|
| QBLANK | 0x0F = Code memory and data EEPROM are NOT blank 0xF0 = Code memory and data EEPROM are blank |
| QVER | 0xMN, where programming executive software version = M.N (i.e., 0x32 means software version 3.2) |

When the programming executive processes any command other than a Query, the QE_Code represents an error code. Supported error codes are shown in [Table 9-4](#). If a command is successfully processed, the returned QE_Code is set to 0x0, which indicates that there was no error in the command processing. If the verify of the programming for the `PROGD`, `PROGP` or `PROGC` command fails, the QE_Code is set to 0x1. For all other programming executive errors, the QE_Code is 0x2.

TABLE 9-4: QE_Code FOR NON-QUERY COMMANDS

| QE_Code | Description |
|---------|---------------|
| 0x0 | No error |
| 0x1 | Verify failed |
| 0x2 | Other error |

9.2.4 RESPONSE LENGTH

The response length indicates the length of the programming executive's response in 16-bit words. This field includes the 2 words of the response header.

With the exception of the response for the `READD` and `READP` commands, the length of each response is only 2 words.

The response to the `READD` command is $N + 2$ words, where N is the number of words specified in the `READD` command.

The response to the `READP` command uses the packed instruction word format described in [Section 8.3 "Packed Data Format"](#). When reading an odd number of program memory words (N odd), the response to the `READP` command is $(3 \cdot (N + 1)/2 + 2)$ words. When reading an even number of program memory words (N even), the response to the `READP` command is $(3 \cdot N/2 + 2)$ words.

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11.0 ICSP™ MODE

11.1 ICSP Mode

ICSP mode is a special programming protocol that allows you to read and write to the dsPIC30F programming executive. The ICSP mode is the second (and slower) method used to program the device. This mode also has the ability to read the contents of executive memory to determine whether the programming executive is present. This capability is accomplished by applying control codes and instructions serially to the device using pins PGC and PGD.

In ICSP mode, the system clock is taken from the PGC pin, regardless of the device's oscillator Configuration bits. All instructions are first shifted serially into an internal buffer, then loaded into the Instruction register and executed. No program fetching occurs from internal memory. Instructions are fed in 24 bits at a time. PGD is used to shift data in and PGC is used as both the serial shift clock and the CPU execution clock.

Data is transmitted on the rising edge and latched on the falling edge of PGC. For all data transmissions, the Least Significant bit (LSb) is transmitted first.

Note 1: During ICSP operation, the operating frequency of PGC must not exceed 5 MHz.

2: Because ICSP is slower, it is recommended that only Enhanced ICSP (E-ICSP) mode be used for device programming, as described in [Section 5.1 "Overview of the Programming Process"](#).

11.2 ICSP Operation

Upon entry into ICSP mode, the CPU is idle. Execution of the CPU is governed by an internal state machine. A 4-bit control code is clocked in using PGC and PGD, and this control code is used to command the CPU (see [Table 11-1](#)).

The SIX control code is used to send instructions to the CPU for execution, while the REGOUT control code is used to read data out of the device via the VISI register. The operation details of ICSP mode are provided in [Section 11.2.1 "SIX Serial Instruction Execution"](#) and [Section 11.2.2 "REGOUT Serial Instruction Execution"](#).

TABLE 11-1: CPU CONTROL CODES IN ICSP™ MODE

| 4-bit Control Code | Mnemonic | Description |
|--------------------|----------|--|
| 0000b | SIX | Shift in 24-bit instruction and execute. |
| 0001b | REGOUT | Shift out the VISI register. |
| 0010b-1111b | N/A | Reserved. |

11.2.1 SIX SERIAL INSTRUCTION EXECUTION

The SIX control code allows execution of dsPIC30F assembly instructions. When the SIX code is received, the CPU is suspended for 24 clock cycles as the instruction is then clocked into the internal buffer. Once the instruction is shifted in, the state machine allows it to be executed over the next four clock cycles. While the received instruction is executed, the state machine simultaneously shifts in the next 4-bit command (see [Figure 11-2](#)).

Note 1: Coming out of the ICSP entry sequence, the first 4-bit control code is always forced to SIX and a forced NOP instruction is executed by the CPU. Five additional PGC clocks are needed on start-up, thereby resulting in a 9-bit SIX command instead of the normal 4-bit SIX command. After the forced SIX is clocked in, ICSP operation resumes as normal (the next 24 clock cycles load the first instruction word to the CPU). See [Figure 11-1](#) for details.

2: TBLRDH, TBLRDL, TBLWTH and TBLWTL instructions must be followed by a NOP instruction.

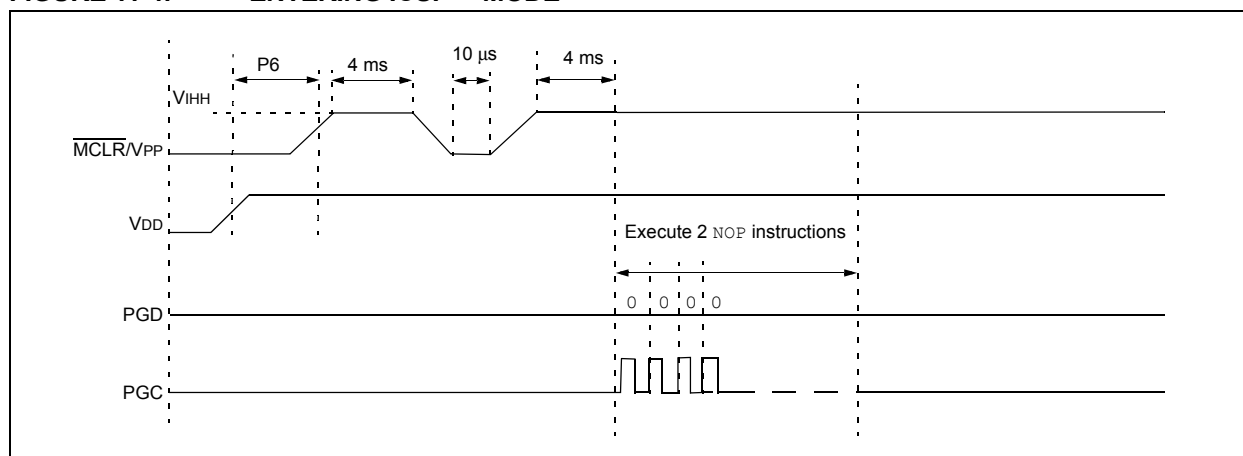
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11.3 Entering ICSP Mode

The ICSP mode is entered by holding PGC and PGD low, raising MCLR/VPP to VIH (high voltage), and then performing additional steps as illustrated in Figure 11-4.

- Note 1:** The sequence that places the device into ICSP mode places all unused I/O pins to the high-impedance state.
- 2:** Once ICSP mode is entered, the PC is set to 0x0 (the Reset vector).
- 3:** Before leaving the Reset vector, execute two GOTO instructions, followed by a single NOP instruction must be executed.

FIGURE 11-4: ENTERING ICSP™ MODE



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Table 11-4 shows the ICSP programming process for bulk-erasing program memory. This process includes the ICSP command code, which must be transmitted (for each instruction) to the Least Significant bit first using the PGC and PGD pins (see Figure 11-2).

If an individual Segment Erase operation is required, the NVMCON value must be replaced by the value for the corresponding Segment Erase operation.

Note: Program memory must be erased before writing any data to program memory.

TABLE 11-4: SERIAL INSTRUCTION EXECUTION FOR BULK ERASING PROGRAM MEMORY (ONLY IN NORMAL-VOLTAGE SYSTEMS)

| Command (Binary) | Data (Hexadecimal) | Description |
|---|--------------------|----------------------|
| Step 1: Exit the Reset vector. | | |
| 0000 | 040100 | GOTO 0x100 |
| 0000 | 040100 | GOTO 0x100 |
| 0000 | 000000 | NOP |
| Step 2: Set NVMCON to program the FBS Configuration register.⁽¹⁾ | | |
| 0000 | 24008A | MOV #0x4008, W10 |
| 0000 | 883B0A | MOV W10, NVMCON |
| Step 3: Initialize the TBLPAG and write pointer (W7) for TBLWT instruction for Configuration register.⁽¹⁾ | | |
| 0000 | 200F80 | MOV #0xF8, W0 |
| 0000 | 880190 | MOV W0, TBLPAG |
| 0000 | 200067 | MOV #0x6, W7 |
| Step 4: Load the Configuration Register data to W6.⁽¹⁾ | | |
| 0000 | EB0300 | CLR W6 |
| 0000 | 000000 | NOP |
| Step 5: Load the Configuration Register write latch. Advance W7 to point to next Configuration register.⁽¹⁾ | | |
| 0000 | BB1B86 | TBLWTL W6, [W7++] |
| Step 6: Unlock the NVMCON for programming the Configuration register.⁽¹⁾ | | |
| 0000 | 200558 | MOV #0x55, W8 |
| 0000 | 200AA9 | MOV #0xAA, W9 |
| 0000 | 883B38 | MOV W8, NVMKEY |
| 0000 | 883B39 | MOV W9, NVMKEY |
| Step 7: Initiate the programming cycle.⁽¹⁾ | | |
| 0000 | A8E761 | BSET NVMCON, #WR |
| 0000 | 000000 | NOP |
| 0000 | 000000 | NOP |
| — | — | Externally time 2 ms |
| 0000 | 000000 | NOP |
| 0000 | 000000 | NOP |
| 0000 | A9E761 | BCLR NVMCON, #WR |
| 0000 | 000000 | NOP |
| 0000 | 000000 | NOP |
| Step 8: Repeat steps 5-7 one time to program 0x0000 to RESERVED2 Configuration register.⁽¹⁾ | | |
| Step 9: Set the NVMCON to erase all Program Memory. | | |
| 00000 | 2407FA | MOV #0x407F, W10 |
| 0000 | 883B0A | MOV W10, NVMCON |
| Step 10: Unlock the NVMCON for programming. | | |

Note 1: Steps 2-8 are only required for the dsPIC30F5011/5013 devices. These steps may be skipped for all other devices in the dsPIC30F family.

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TABLE 11-5: SERIAL INSTRUCTION EXECUTION FOR ERASING PROGRAM MEMORY (EITHER IN LOW-VOLTAGE OR NORMAL-VOLTAGE SYSTEMS) (CONTINUED)

| Command (Binary) | Data (Hexadecimal) | Description |
|--|-----------------------|---|
| Step 18: Unlock the NVMCON to erase 1 row of data memory. | | |
| 0000 | 200558 | MOV #0x55, W8 |
| 0000 | 883B38 | MOV W8, NVMKEY |
| 0000 | 200AA9 | MOV #0xAA, W9 |
| 0000 | 883B39 | MOV W9, NVMKEY |
| Step 19: Initiate the erase cycle. | | |
| 0000 | A8E761 | BSET NVMCON, #WR |
| 0000 | 000000 | NOP |
| 0000 | 000000 | NOP |
| — | — | Externally time 'P13a' ms (see Section 13.0 “AC/DC Characteristics and Timing Requirements”) |
| 0000 | 000000 | NOP |
| 0000 | 000000 | NOP |
| 0000 | A9E761 | BCLR NVMCON, #WR |
| 0000 | 000000 | NOP |
| 0000 | 000000 | NOP |
| Step 20: Update the row address stored in NVMADR. | | |
| 0000 | 430307 | ADD W6, W7, W6 |
| 0000 | 883B16 | MOV W6, NVMADR |
| Step 21: Reset device internal PC. | | |
| 0000 | 040100 | GOTO 0x100 |
| 0000 | 000000 | NOP |
| Step 22: Repeat Steps 17-21 until all rows of data memory are erased. | | |

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11.8 Writing Code Memory

The procedure for writing code memory is similar to the procedure for clearing the Configuration registers, except that 32 instruction words are programmed at a time. To facilitate this operation, working registers W0:W5 are used as temporary holding registers for the data to be programmed.

Table 11-8 shows the ICSP programming details, including the serial pattern with the ICSP command code, which must be transmitted Least Significant bit first using the PGC and PGD pins (see Figure 11-2). In Step 1, the Reset vector is exited. In Step 2, the NVMCON register is initialized for single-panel programming of code memory. In Step 3, the 24-bit starting destination address for programming is loaded into the TBLPAG register and W7 register. The upper byte of the starting destination address is stored to TBLPAG, while the lower 16 bits of the destination address are stored to W7.

To minimize the programming time, the same packed instruction format that the programming executive uses is utilized (Figure 8-2). In Step 4, four packed instruction words are stored to working registers W0:W5 using the MOV instruction and the read pointer W6 is initialized. The contents of W0:W5 holding the packed instruction word data is shown in Figure 11-4.

In Step 5, eight TBLWT instructions are used to copy the data from W0:W5 to the write latches of code memory. Since code memory is programmed 32 instruction words at a time, Steps 4 and 5 are repeated eight times to load all the write latches (Step 6).

After the write latches are loaded, programming is initiated by writing to the NVMKEY and NVMCON registers in Steps 7 and 8. In Step 9, the internal PC is reset to 0x100. This is a precautionary measure to prevent the PC from incrementing into unimplemented memory when large devices are being programmed. Lastly, in Step 10, Steps 2-9 are repeated until all of code memory is programmed.

FIGURE 11-5: PACKED INSTRUCTION WORDS IN W0:W5

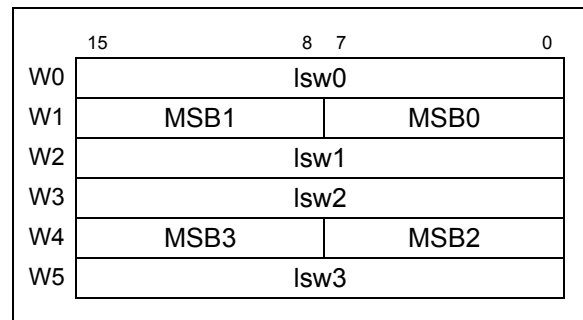


TABLE 11-8: SERIAL INSTRUCTION EXECUTION FOR WRITING CODE MEMORY

| Command (Binary) | Data (Hexadecimal) | Description |
|--|--------------------|------------------------------------|
| Step 1: Exit the Reset vector. | | |
| 0000 | 040100 | GOTO 0x100 |
| 0000 | 040100 | GOTO 0x100 |
| 0000 | 000000 | NOP |
| Step 2: Set the NVMCON to program 32 instruction words. | | |
| 0000 | 24001A | MOV #0x4001, W10 |
| 0000 | 883B0A | MOV W10, NVMCON |
| Step 3: Initialize the write pointer (W7) for TBLWT instruction. | | |
| 0000 | 200xx0 | MOV #<DestinationAddress23:16>, W0 |
| 0000 | 880190 | MOV W0, TBLPAG |
| 0000 | 2xxxx7 | MOV #<DestinationAddress15:0>, W7 |
| Step 4: Initialize the read pointer (W6) and load W0:W5 with the next 4 instruction words to program. | | |
| 0000 | 2xxxx0 | MOV #<LSW0>, W0 |
| 0000 | 2xxxx1 | MOV #<MSB1:MSB0>, W1 |
| 0000 | 2xxxx2 | MOV #<LSW1>, W2 |
| 0000 | 2xxxx3 | MOV #<LSW2>, W3 |
| 0000 | 2xxxx4 | MOV #<MSB3:MSB2>, W4 |
| 0000 | 2xxxx5 | MOV #<LSW3>, W5 |

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11.12 Reading Data Memory

The procedure for reading data memory is similar to that of reading code memory, except that 16-bit data words are read instead of 24-bit words. Since less data is read in each operation, only working registers W0:W3 are used as temporary holding registers for the data to be read.

Table 11-12 shows the ICSP programming details for reading data memory. Note that the TBLPAG register is hard-coded to 0x7F (the upper byte address of all locations of data memory).

TABLE 11-12: SERIAL INSTRUCTION EXECUTION FOR READING DATA MEMORY

| Command (Binary) | Data (Hexadecimal) | Description |
|---|--------------------|-------------------------------------|
| Step 1: Exit the Reset vector. | | |
| 0000 | 040100 | GOTO 0x100 |
| 0000 | 040100 | GOTO 0x100 |
| 0000 | 000000 | NOP |
| Step 2: Initialize TBLPAG and the read pointer (W6) for TBLRD instruction. | | |
| 0000 | 2007F0 | MOV #0x7F, W0 |
| 0000 | 880190 | MOV W0, TBLPAG |
| 0000 | 2xxxx6 | MOV #<SourceAddress15:0>, W6 |
| Step 3: Initialize the write pointer (W7) and store the next four locations of code memory to W0:W5. | | |
| 0000 | EB0380 | CLR W7 |
| 0000 | 000000 | NOP |
| 0000 | BA1BB6 | TBLRDL [W6++], [W7++] |
| 0000 | 000000 | NOP |
| 0000 | 000000 | NOP |
| 0000 | BA1BB6 | TBLRDL [W6++], [W7++] |
| 0000 | 000000 | NOP |
| 0000 | 000000 | NOP |
| 0000 | BA1BB6 | TBLRDL [W6++], [W7++] |
| 0000 | 000000 | NOP |
| 0000 | 000000 | NOP |
| 0000 | BA1BB6 | TBLRDL [W6++], [W7++] |
| 0000 | 000000 | NOP |
| 0000 | 000000 | NOP |
| Step 4: Output W0:W5 using the VISI register and REGOUT command. | | |
| 0000 | 883C20 | MOV W0, VISI |
| 0000 | 000000 | NOP |
| 0001 | <VISI> | Clock out contents of VISI register |
| 0000 | 000000 | NOP |
| 0000 | 883C21 | MOV W1, VISI |
| 0000 | 000000 | NOP |
| 0001 | <VISI> | Clock out contents of VISI register |
| 0000 | 000000 | NOP |
| 0000 | 883C22 | MOV W2, VISI |
| 0000 | 000000 | NOP |
| 0001 | <VISI> | Clock out contents of VISI register |
| 0000 | 000000 | NOP |
| 0000 | 883C23 | MOV W3, VISI |
| 0000 | 000000 | NOP |
| 0001 | <VISI> | Clock out contents of VISI register |
| 0000 | 000000 | NOP |
| Step 5: Reset device internal PC. | | |
| 0000 | 040100 | GOTO 0x100 |
| 0000 | 000000 | NOP |
| Step 6: Repeat steps 3-5 until all desired data memory is read. | | |

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11.13 Reading the Application ID Word

The application ID word is stored at address 0x8005BE in executive code memory. To read this memory location, you must use the SIX control code to move this program memory location to the VISI register. The REGOUT control code must then be used to clock the contents of the VISI register out of the device. The corresponding control and instruction codes that must be serially transmitted to the device to perform this operation are shown in [Table 11-13](#).

Once the programmer has clocked-out the application ID word, it must be inspected. If the application ID has the value 0xBB, the programming executive is resident in memory and the device can be programmed using the mechanism described in [Section 5.0 “Device Programming”](#). However, if the application ID has any other value, the programming executive is not resident in memory. It must be loaded to memory before the device can be programmed. The procedure for loading the programming executive to the memory is described in [Section 12.0 “Programming the Programming Executive to Memory”](#).

11.14 Exiting ICSP Mode

After confirming that the programming executive is resident in memory, or loading the programming executive, ICSP mode is exited by removing power to the device or bringing MCLR to V_{IL}. Programming can then take place by following the procedure outlined in [Section 5.0 “Device Programming”](#).

TABLE 11-13: SERIAL INSTRUCTION EXECUTION FOR READING THE APPLICATION ID WORD

| Command (Binary) | Data (Hexadecimal) | Description |
|---|-----------------------|---|
| Step 1: Exit the Reset vector. | | |
| 0000 | 040100 | GOTO 0x100 |
| 0000 | 040100 | GOTO 0x100 |
| 0000 | 000000 | NOP |
| Step 2: Initialize TBLPAG and the read pointer (W0) for TBLRD instruction. | | |
| 0000 | 200800 | MOV #0x80, W0 |
| 0000 | 880190 | MOV W0, TBLPAG |
| 0000 | 205BE0 | MOV #0x5BE, W0 |
| 0000 | 207841 | MOV VISI, W1 |
| 0000 | 000000 | NOP |
| 0000 | BA0890 | TBLRDL [W0], [W1] |
| 0000 | 000000 | NOP |
| 0000 | 000000 | NOP |
| Step 3: Output the VISI register using the REGOUT command. | | |
| 0001 | <VISI> | Clock out contents of the VISI register |
| 0000 | 000000 | NOP |

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13.0 AC/DC CHARACTERISTICS AND TIMING REQUIREMENTS

TABLE 13-1: AC/DC CHARACTERISTICS

| AC/DC CHARACTERISTICS | | | Standard Operating Conditions (unless otherwise stated) Operating Temperature: 25° C is recommended | | | |
|-----------------------|---------|---|---|---------|---------------|--------------------------------|
| Param. No. | Sym | Characteristic | Min | Max | Units | Conditions |
| D110 | VIHH | High Programming Voltage on $\overline{\text{MCLR}}/\text{VPP}$ | 9.00 | 13.25 | V | — |
| D112 | IPP | Programming Current on $\overline{\text{MCLR}}/\text{VPP}$ | — | 300 | μA | — |
| D113 | IDDP | Supply Current during programming | — | 30 | mA | Row Erase Program memory |
| | | | — | 30 | mA | Row Erase Data EEPROM |
| | | | — | 30 | mA | Bulk Erase |
| D001 | VDD | Supply voltage | 2.5 | 5.5 | V | — |
| D002 | VDDBULK | Supply voltage for Bulk Erase programming | 4.5 | 5.5 | V | — |
| D031 | VIL | Input Low Voltage | VSS | 0.2 VSS | V | — |
| D041 | VIH | Input High Voltage | 0.8 VDD | VDD | V | — |
| D080 | VOL | Output Low Voltage | — | 0.6 | V | IOL = 8.5 mA |
| D090 | VOH | Output High Voltage | VDD - 0.7 | — | V | IOH = -3.0 mA |
| D012 | CIO | Capacitive Loading on I/O Pin (PGD) | — | 50 | pF | To meet AC specifications |
| P1 | TCLK | Serial Clock (PGC) period | 50 | — | ns | ICSP™ mode |
| | | | 1 | — | μs | Enhanced ICSP mode |
| P1a | TCLKL | Serial Clock (PGC) low time | 20 | — | ns | ICSP mode |
| | | | 400 | — | ns | Enhanced ICSP mode |
| P1b | TCLKH | Serial Clock (PGC) high time | 20 | — | ns | ICSP mode |
| | | | 400 | — | ns | Enhanced ICSP mode |
| P2 | TSET1 | Input Data Setup Timer to PGC ↓ | 15 | — | ns | — |
| P3 | THLD1 | Input Data Hold Time from PGC ↓ | 15 | — | ns | — |
| P4 | TDLY1 | Delay between 4-bit command and command operand | 20 | — | ns | — |
| P4a | TDLY1a | Delay between 4-bit command operand and next 4-bit command | 20 | — | ns | — |
| P5 | TDLY2 | Delay between last PGC ↓ of command to first PGC ↑ of VISI output | 20 | — | ns | — |
| P6 | TSET2 | VDD ↑ setup time to $\overline{\text{MCLR}}/\text{VPP}$ | 100 | — | ns | — |
| P7 | THLD2 | Input data hold time from $\overline{\text{MCLR}}/\text{VPP}$ ↑ | 2 | — | μs | ICSP mode |
| | | | 5 | — | ms | Enhanced ICSP mode |
| P8 | TDLY3 | Delay between last PGC ↓ of command word to PGD driven ↑ by programming executive | 20 | — | μs | — |
| P9a | TDLY4 | Programming Executive Command processing time | 10 | — | μs | — |

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TABLE A-1: CHECKSUM COMPUTATION (CONTINUED)

| Device | Read Code Protection | Checksum Computation | Erased Value | Value with 0xAAAAAA at 0x0 and Last Code Address |
|---------------|----------------------|----------------------|--------------|--|
| dsPIC30F5016 | Disabled | CFGB+SUM(0:00AFFF) | 0xFC06 | 0xFA08 |
| | Enabled | CFGB | 0x0404 | 0x0404 |
| dsPIC30F6010 | Disabled | CFGB+SUM(0:017FFF) | 0xC406 | 0xC208 |
| | Enabled | CFGB | 0x0404 | 0x0404 |
| dsPIC30F6010A | Disabled | CFGB+SUM(0:017FFF) | 0xC406 | 0xC208 |
| | Enabled | CFGB | 0x0404 | 0x0404 |
| dsPIC30F6011 | Disabled | CFGB+SUM(0:015FFF) | 0xF406 | 0xF208 |
| | Enabled | CFGB | 0x0404 | 0x0404 |
| dsPIC30F6011A | Disabled | CFGB+SUM(0:015FFF) | 0xF406 | 0xF208 |
| | Enabled | CFGB | 0x0404 | 0x0404 |
| dsPIC30F6012 | Disabled | CFGB+SUM(0:017FFF) | 0xC406 | 0xC208 |
| | Enabled | CFGB | 0x0404 | 0x0404 |
| dsPIC30F6012A | Disabled | CFGB+SUM(0:017FFF) | 0xC406 | 0xC208 |
| | Enabled | CFGB | 0x0404 | 0x0404 |
| dsPIC30F6013 | Disabled | CFGB+SUM(0:015FFF) | 0xF406 | 0xF208 |
| | Enabled | CFGB | 0x0404 | 0x0404 |
| dsPIC30F6013A | Disabled | CFGB+SUM(0:015FFF) | 0xF406 | 0xF208 |
| | Enabled | CFGB | 0x0404 | 0x0404 |
| dsPIC30F6014 | Disabled | CFGB+SUM(0:017FFF) | 0xC406 | 0xC208 |
| | Enabled | CFGB | 0x0404 | 0x0404 |
| dsPIC30F6014A | Disabled | CFGB+SUM(0:017FFF) | 0xC406 | 0xC208 |
| | Enabled | CFGB | 0x0404 | 0x0404 |
| dsPIC30F6015 | Disabled | CFGB+SUM(0:017FFF) | 0xC406 | 0xC208 |
| | Enabled | CFGB | 0x0404 | 0x0404 |

Item Description:

SUM(a:b) = Byte sum of locations a to b inclusive (all 3 bytes of code memory)

CFGB = **Configuration Block (masked)** = Byte sum of ((FOSC&0xC10F) + (FWDT&0x803F) + (FBORPOR&0x87B3) + (FBS&0x310F) + (FSS&0x330F) + (FGS&0x0007) + (FICD&0xC003))

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NOTES: